

Intra coil
Insulation

Polyimide
Q @ 300 MHz
(Kapton)
Top Coil = 20

Bottom Coil =

15
Technology
CMOS

0.35 μm & 0.6
μm

Figure 2. Cross section of iCoupler transformer coil.

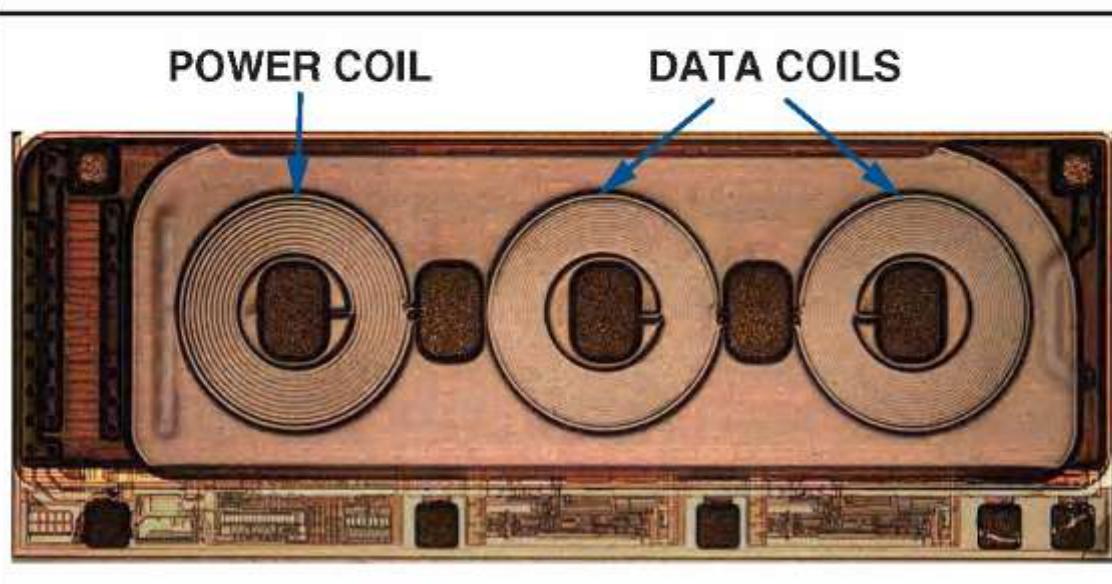
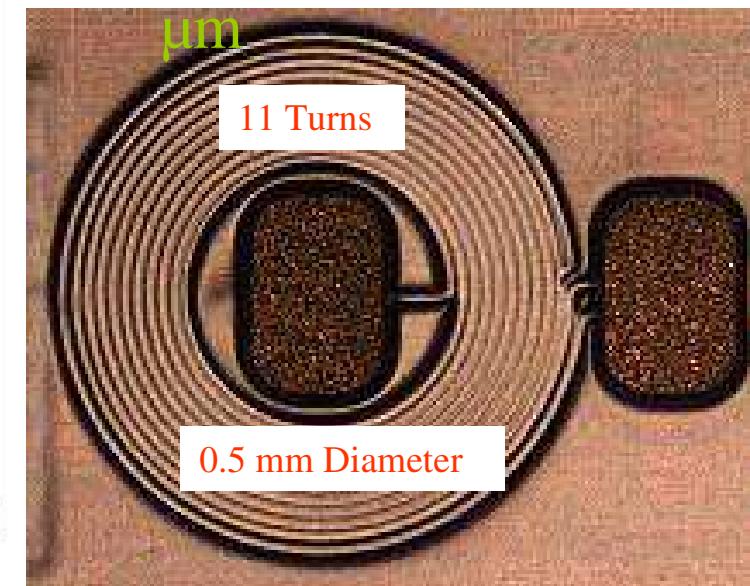
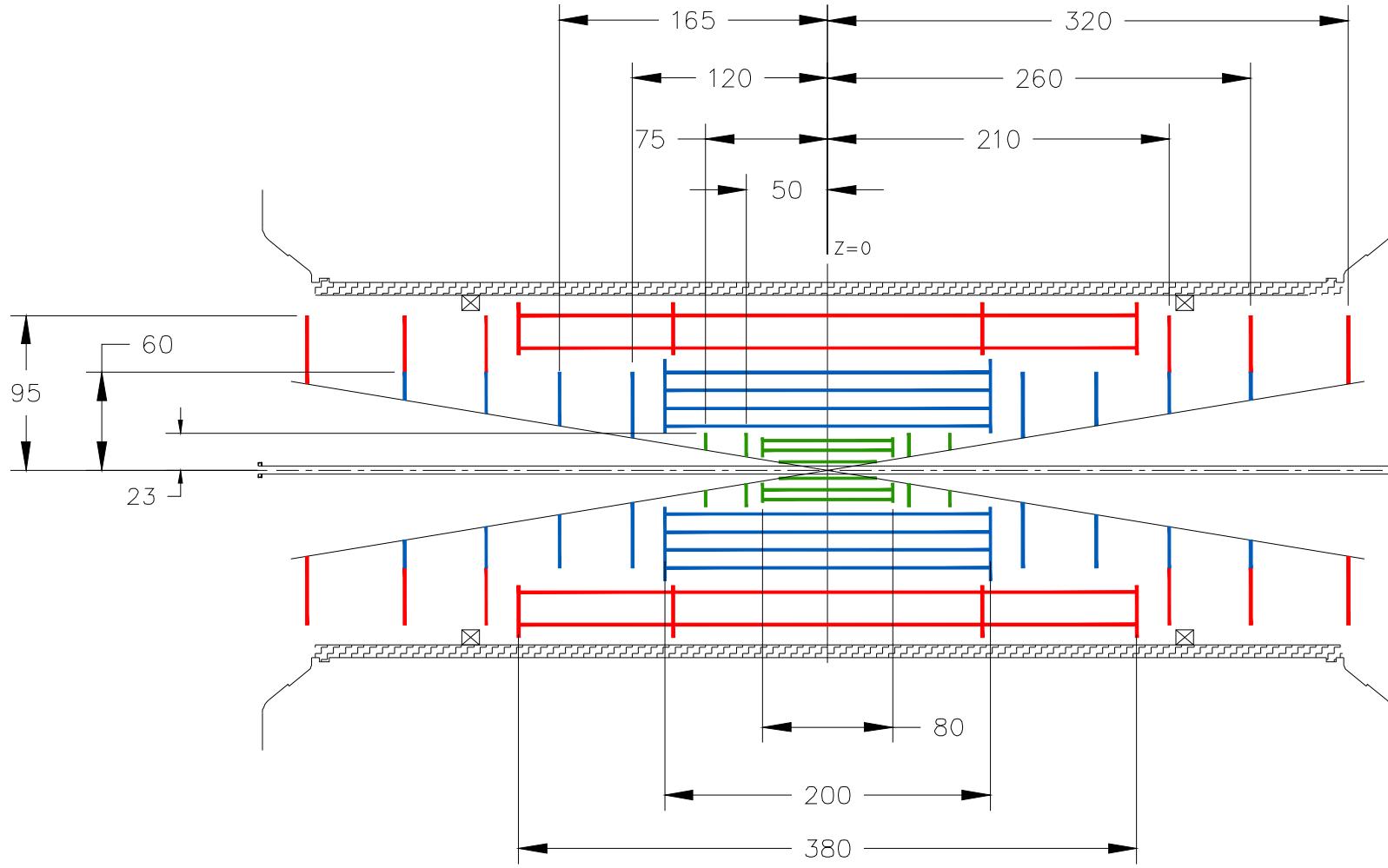


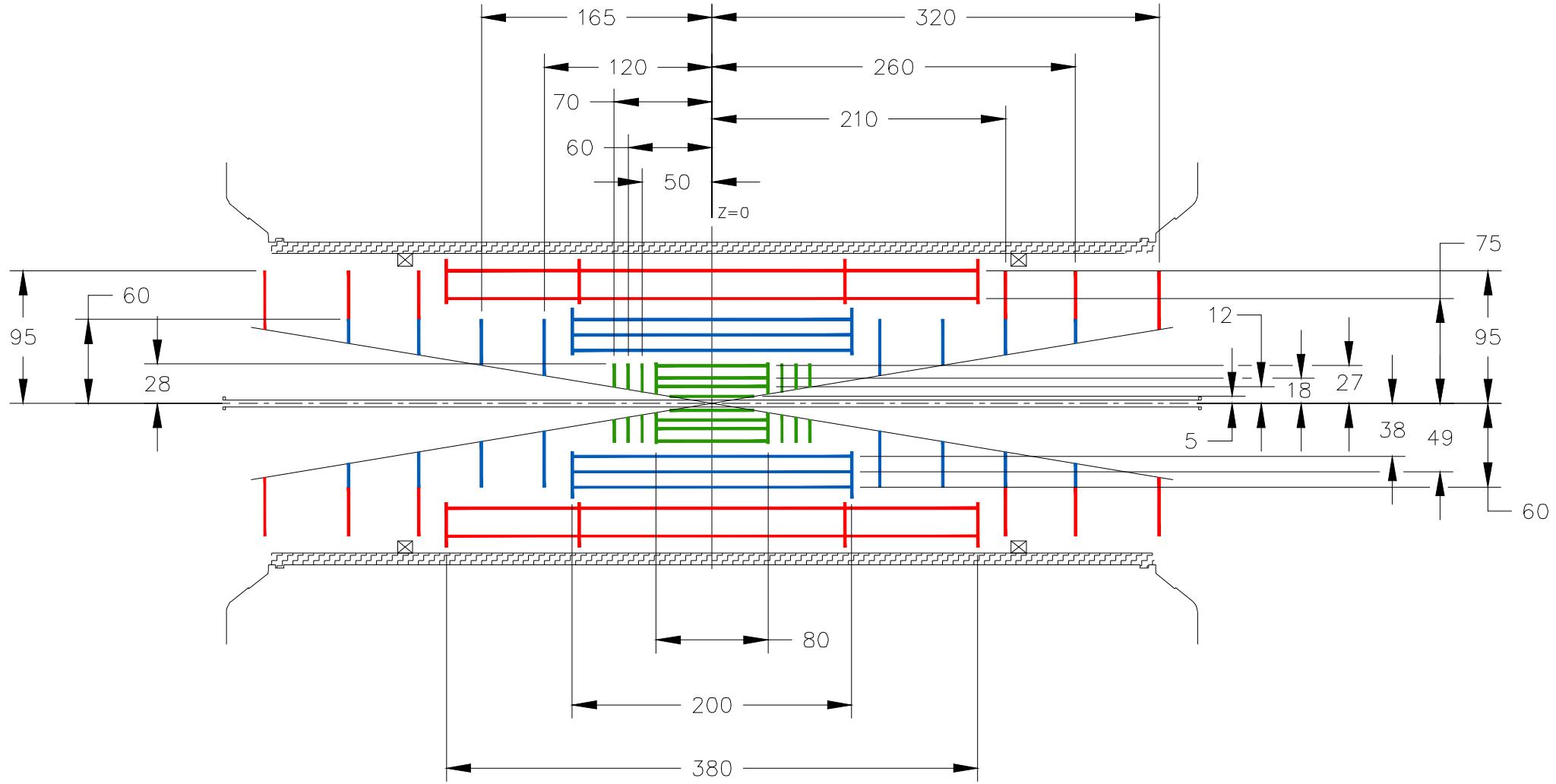
Figure 3. Photograph of transformer die showing the power transformer coil and the two data transformer coils.



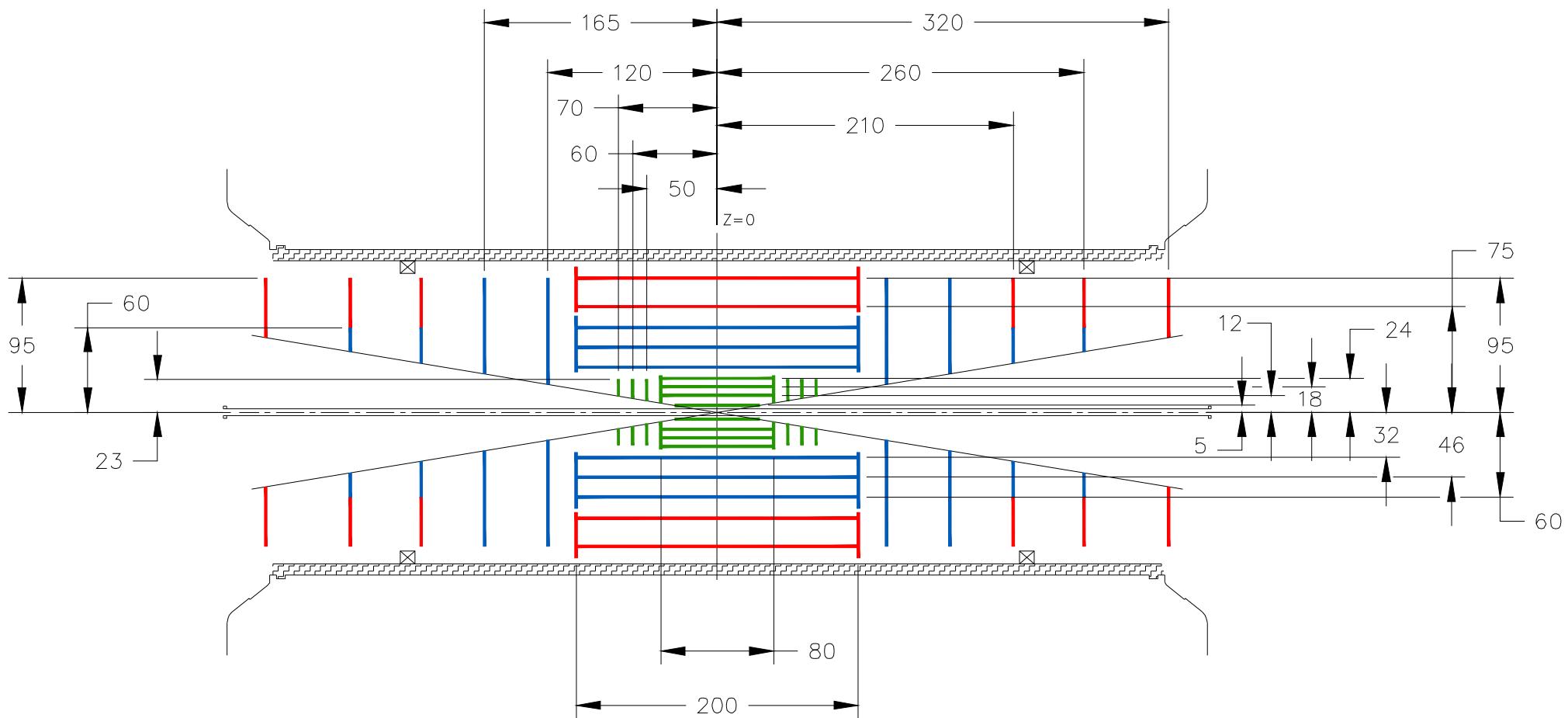
ID Strawman Layout 3+4+2 (P+SS+LS)



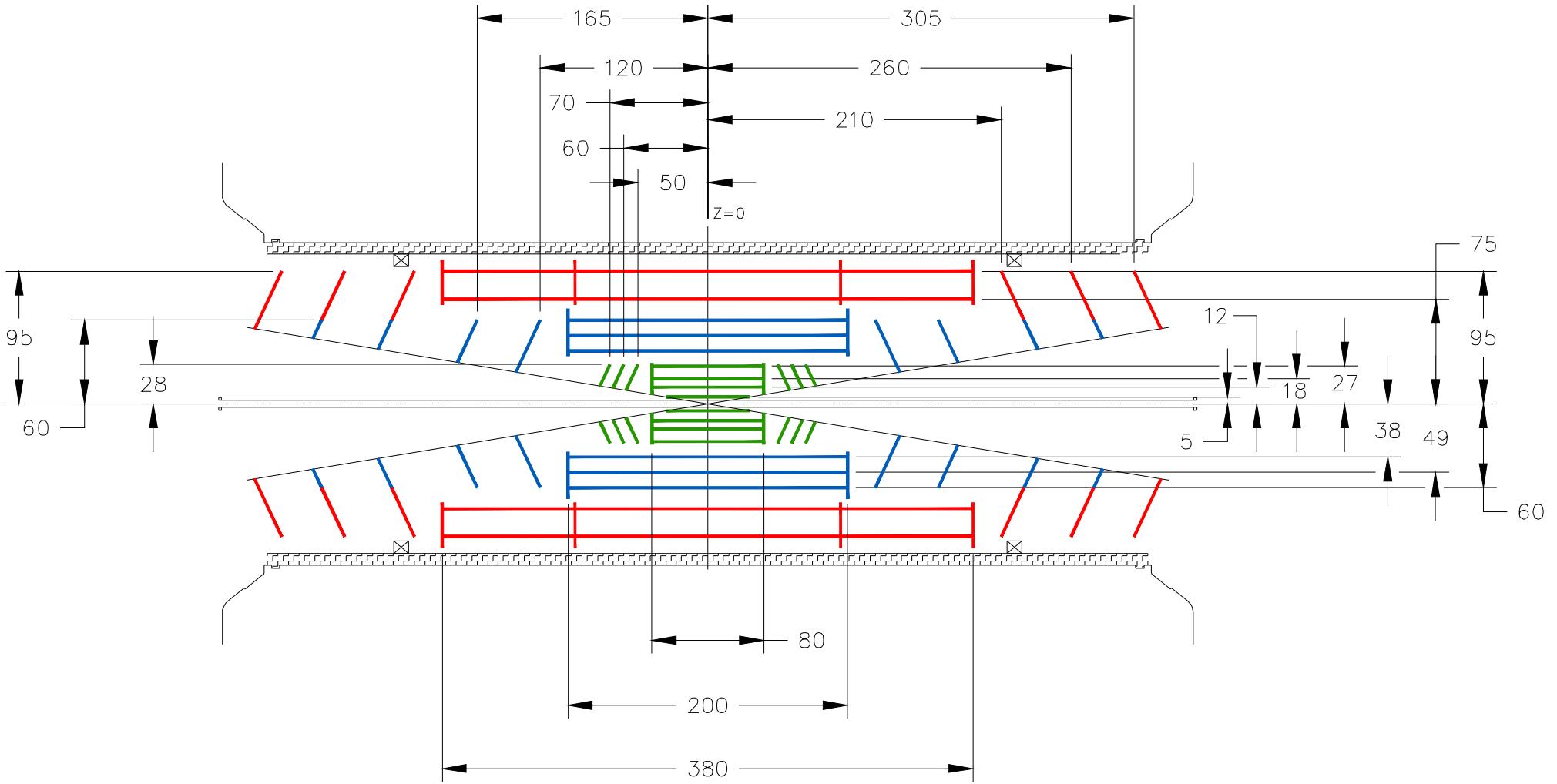
4+3+2 (Pixel, SS, LS) - Strawman



SS/LS FIXED LENGTH



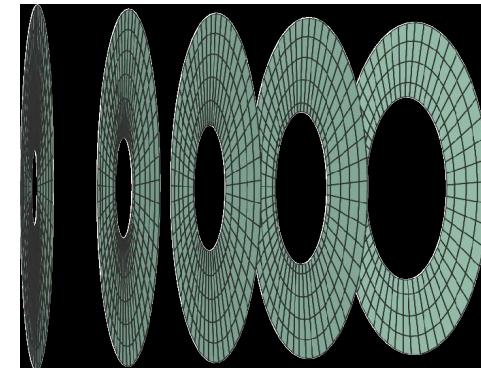
4+3+2 25 Degree Cone Ends



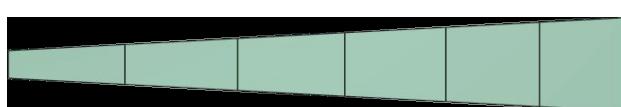
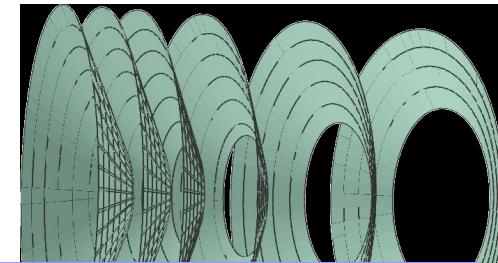
BROOKHAVEN
NATIONAL LABORATORY

Conical-flat disk

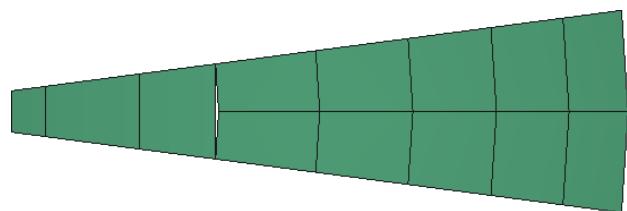
Internal wheel		Rout (cm)	Rin (cm)	N. staves	N. rings	Area (cm ²)
Cone wheel	1 row stave	95,0	24,4	61,0	7,0	32100,5
Flat wheel	1 row stave	95,0	19,8	55,0	6,0	26949,7
Cone wheel	2 row stave	95,0	24,4	24,0	9,0	34190,1
Flat wheel	2 row stave	95,0	19,8	24,0	8,0	28709,4



- To reach the same inner radio more rings (more silicon) is needed with conical disk.
- 2 row staves more complicated to assemble, but smaller number/disk needed.



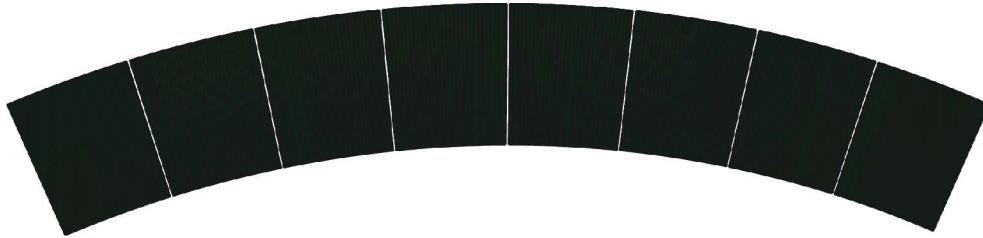
To narrow wafer for low radio, small pitch, place the hybrids an issue



Gap at a fixed radio and larger diversity of sensors

In the concept of radial staves the implementation of services may look “easy”, it looks natural at a first glance.

Circumferential stave



- 8 round edges wafer to built a circumferential stave.
- Pitch fixed to 80 µm at half height of the wafer.
- 8 chips per wafer
- All strips in a ring have the same length.
- One type of sensor per ring.
- Cones difficult to implement.

Ring	Up width (cm)	Bot. width (cm)	Number Staves
1	8,7	7,2	9
2	8,7	7,6	8
3	8,6	7,4	7
4	8,6	7,0	6
5	8,4	6,6	5
6	10,9	8,3	3
7	8,3	5,1	3

TOTAL = 41 staves for the more internal disk

Main problem: how to
“route” the services out of
the staves.

Elastic Contact Structures

ELASTeo®



Source: Infineon

ClawConnect™ made of StressedMetall™:



Source: Fraunhofer IAP
University of Bayreuth
Institute of Microtechnology

Source: Nanoleaf,
Xerox Co., PARC



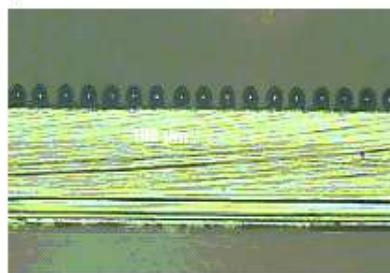
J-shaped planar microspring



Source: Georgia Tech
Deposition:
High Density Electroless Ni / Wet Electroless Plating
Phone: +49 703 3400-123
E-mail: clawconnect@infineon.de

Future Requirements: Thin Silicon

Thinning of bumped wafers:

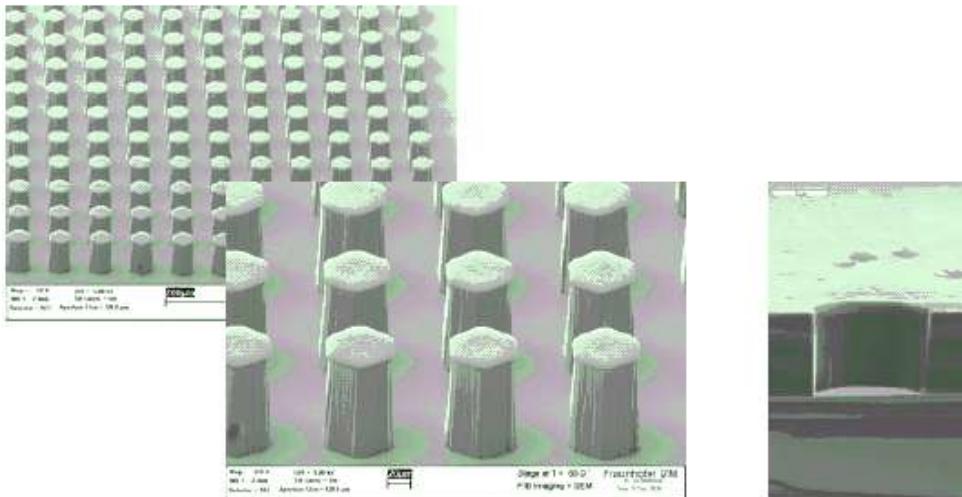


Source: Fraunhofer IAP
University of Bayreuth
Institute of Microtechnology

Nanoleaf
Institute of Microtechnology and Nanotechnology

Deposition:
High Density Electroless Ni / Wet Electroless Plating
Phone: +49 703 3400-123
E-mail: clawconnect@infineon.de

Cu Pillar Bumps (Height: 80 µm, Diameter: 60 µm)

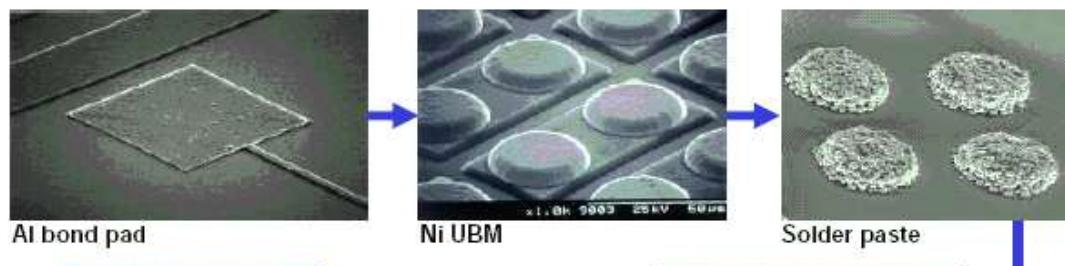


TU
Technische Universität Berlin
Research Center of
Microelectronic Technologies

raumfeld
Zentrum für
Zwei- und Mehrphasen
Verarbeitungstechniken

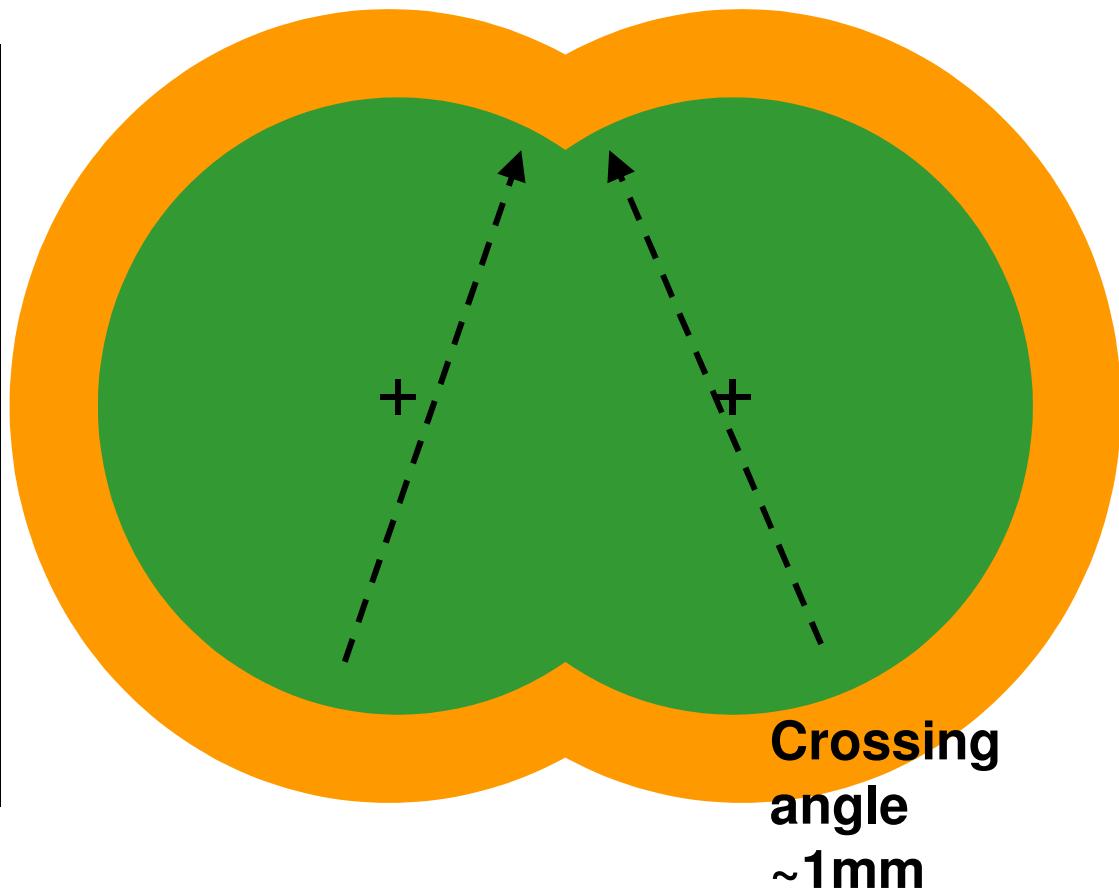
Department:
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Phone: +49-(0)30-6403-124
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Process Flow - Stencil Printing



Beam stay-clear radius composition

Component		mm
Separation	5	2.5
Beam size	15	7.5
Closed orbit	-	3
Crossing angle	-	1
TOTAL		14

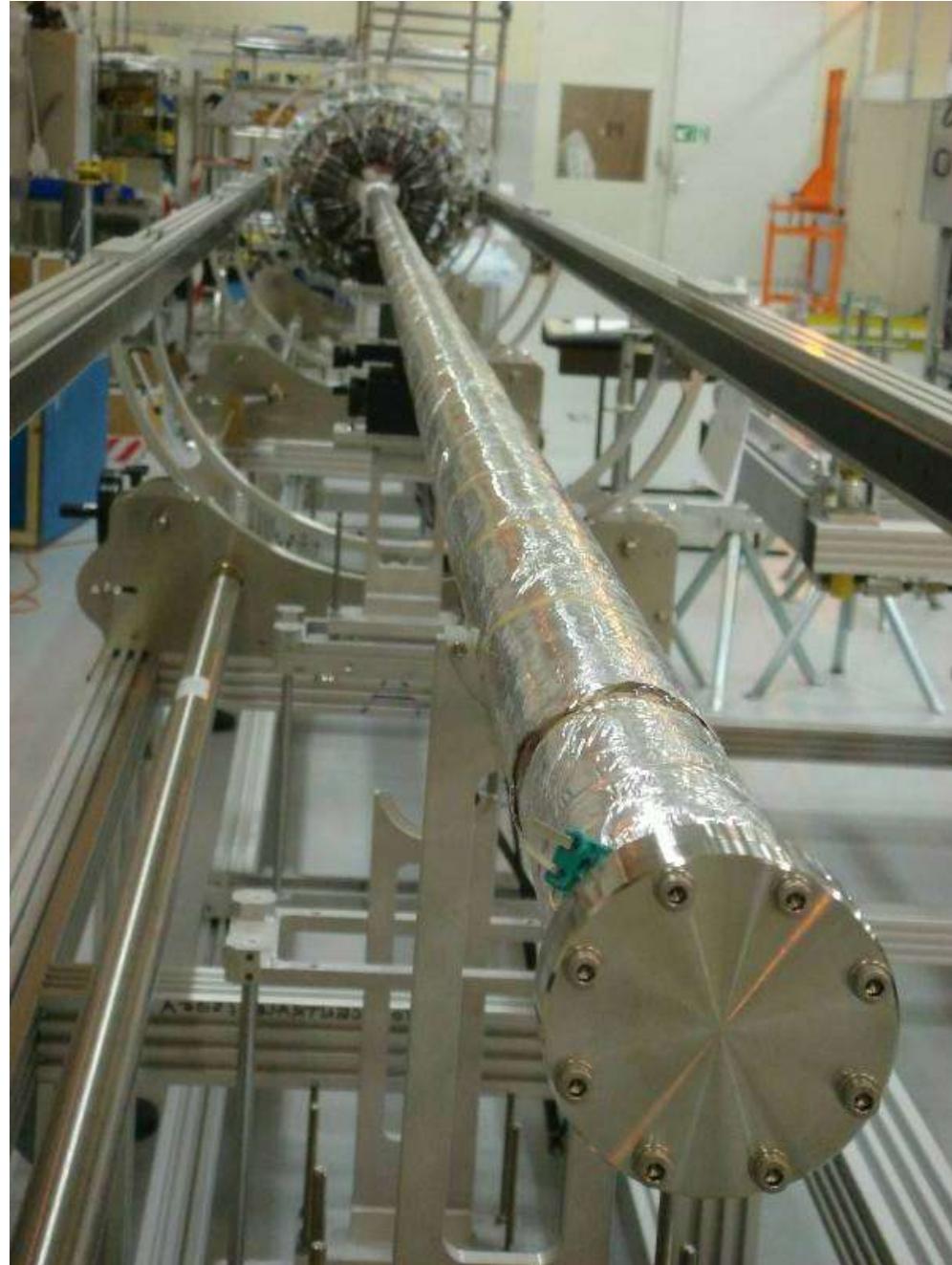


Crossing half-angle of $\sim 200\mu$ rad for upgraded LHC

In forward regions this may be higher for collision optics **Beampipe Diameter for LHe Baseline** (1997 values)

- Survey Precision ~ 2.6mm
 - A given survey target in the tracker region was expected to be placed within 2.6mm of the nominal beam axis with a 2σ (95%) confidence, using the survey techniques planned for ATLAS
- Mechanical construction ~ 2.6mm
 - Tolerances on straightness, circularity, wall thickness, sag under self-weight etc
- Instabilities ~ 9.8mm
 - Stability of the cavern, movements due to electromagnetic forces, thermal expansion

Central beampipe (spare) in final configuration on the pixel assembly bench



SoS Technology Features

